

IN THE ABSTRACT OF THE DISCLOSURE:

Please amend replace the abstract as follow with the following new abstract:

ABSTRACT

A semiconductor integrated circuit has ~~over one semiconductor substrate a~~ nonvolatile memory and a logic circuit which uses information stored in the nonvolatile memory to perform logical operation. The nonvolatile memory comprises bit lines (~~bl and blb~~), word lines (~~wl_n~~), and memory cells (~~20~~). The memory cell comprises MOS transistors (~~M1 and M2~~) whose gate electrodes are connected with a word line. Information storage is carried out according to whether one source/drain electrode of the MOS transistors is connected with a source line (~~cs~~) or floated. During ~~the other~~ periods than a predetermined period in the operation of accessing the memory cell, the potential difference between the source/drain electrodes of the MOS transistors constituting the memory cell is zeroed. ~~Therefore, subthreshold-Subthreshold leakage current is prevented from being passed passing~~ through the memory cell on standby. During the predetermined period in accessing operation, a potential difference is produced between the source/drain electrodes of the MOS transistors. Therefore, the bit line potential can be varied by word line selection.